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Total No. of Pages : 01

Total No. of Questions : 08

M.Tech. (Microelectronics) (Sem.-1)

**MICRO & NANO SCIENCES & TECHNOLOGY**

Subject Code : ME-801

Paper ID : [E0961]

Time : 3 Hrs.

Max. Marks : 100

**INSTRUCTIONS TO CANDIDATES :**

1. Attempt any FIVE questions out of EIGHT question.
2. Each question carries TWENTY marks.

- Q1. a) Describe in detail about density of states in semiconductor devices.  
b) Write a brief note on plasma assisted deposition.
- Q2. Define packaging. What is the need of packaging? Discuss about the package types in detail.
- Q3. a) Explain the process of optical lithography in detail.  
b) Write a brief note on control and anisotropic etch mechanism.
- Q4. a) Discuss about Czochralski crystal growing process in brief.  
b) What is diffusion transport? Also derive the Einstein relation.
- Q5. Discuss in brief about relative plasma etching techniques and equipments.
- Q6. a) Explain CMOS IC technology in brief.  
b) Write a brief note on the concept of growth mechanism and kinetics.
- Q7. a) Discuss annealing shallow junction in detail.  
b) Discuss in brief the properties of plasma.
- Q8. Write short notes on following :
- a) Deposition processes
  - b) Range theory
  - c) Vapor Phase epitaxy
  - d) Molecular Beam epitaxy